



APT50M60JVFR

500V 63A 0.060Ω

POWER MOS V[®] FREDFET

Power MOS V[®] is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V[®] also achieves faster switching speeds through optimized gate layout.



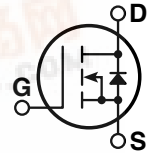
• Popular SOT-227 Package

• Avalanche Energy Rated

• Faster Switching

• FAST RECOVERY BODY DIODE

• Lower Leakage



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT50M60JVFR	UNIT
V_{DSS}	Drain-Source Voltage	500	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	63	Amps
I_{DM}	Pulsed Drain Current ^①	252	
V_{GS}	Gate-Source Voltage Continuous	± 30	Volts
V_{GSM}	Gate-Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	568	Watts
	Linear Derating Factor	4.55	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	63	Amps
E_{AR}	Repetitive Avalanche Energy ^①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ^④	3200	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu A$)	500			Volts
$R_{DS(on)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10V, I_D = 31.5A$)			0.060	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 500V, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 400V, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 5mA$)	2		4	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT50M60JVFR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		10600		pF
C_{oss}	Output Capacitance			1800		
C_{rss}	Reverse Transfer Capacitance			795		
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 250V$ $I_D = 63A @ 25^\circ C$		560		nC
Q_{gs}	Gate-Source Charge			70		
Q_{gd}	Gate-Drain ("Miller") Charge			285		
$t_{d(on)}$	Turn-on Delay Time	RESISTIVE SWITCHING $V_{GS} = 15V$ $V_{DD} = 250V$ $I_D = 63A @ 25^\circ C$ $R_G = 0.6\Omega$		20		ns
t_r	Rise Time			25		
$t_{d(off)}$	Turn-off Delay Time			80		
t_f	Fall Time			10		
E_{on}	Turn-on Switching Energy ⑥	INDUCTIVE SWITCHING @ 25°C $V_{DD} = 333V, V_{GS} = 15V$ $I_D = 63A, R_G = 5\Omega$		1235		μJ
E_{off}	Turn-off Switching Energy			2820		
E_{on}	Turn-on Switching Energy ⑥	INDUCTIVE SWITCHING @ 125°C $V_{DD} = 333V, V_{GS} = 15V$ $I_D = 63A, R_G = 5\Omega$		1700		
E_{off}	Turn-off Switching Energy			2900		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			63	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			252	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -63A$)			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt ⑤			15	V/ns
t_{rr}	Reverse Recovery Time ($I_S = -63A, di/dt = 100A/\mu s$)	$T_j = 25^\circ C$		300	ns
		$T_j = 125^\circ C$		600	
Q_{rr}	Reverse Recovery Charge ($I_S = -63A, di/dt = 100A/\mu s$)	$T_j = 25^\circ C$	2.6		μC
		$T_j = 125^\circ C$	10		
I_{RRM}	Peak Recovery Current ($I_S = -63A, di/dt = 100A/\mu s$)	$T_j = 25^\circ C$	17		Amps
		$T_j = 125^\circ C$	34		

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.22	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

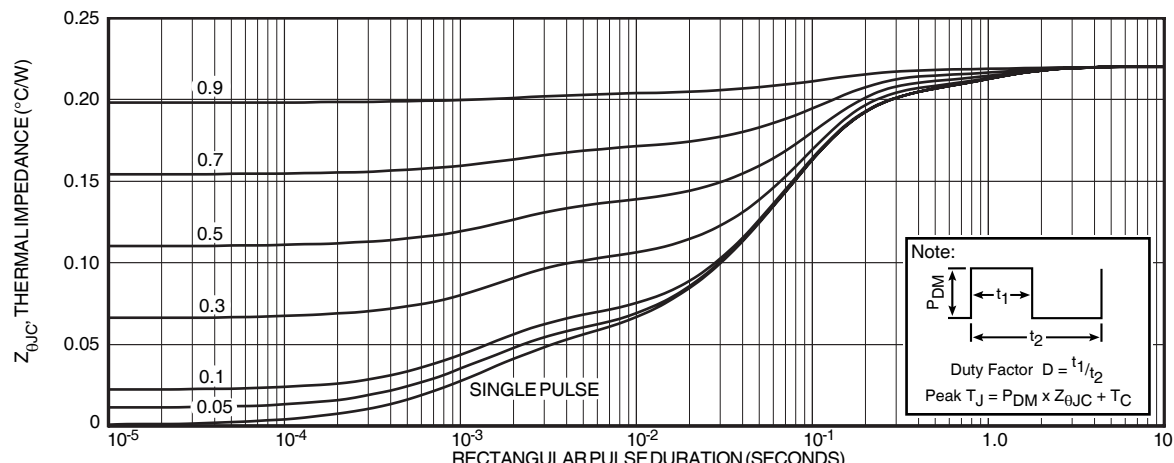
③ See MIL-STD-750 Method 3471

④ Starting $T_j = +25^\circ C$, $L = 1.61mH$, $R_G = 25\Omega$, Peak $I_L = 63A$

⑤ dv/dt numbers reflect the limitations of the test circuit rather than the device itself. $I_S \leq -I_D 63A$ $di/dt \leq 700A/\mu s$ $V_R \leq 500V$ $T_j \leq 150^\circ C$

⑥ E_{on} includes diode reverse recovery. See figures 18, 20.

APT Reserves the right to change, without notice, the specifications and information contained herein.



Typical Performance Curves

APT50M60JVFR

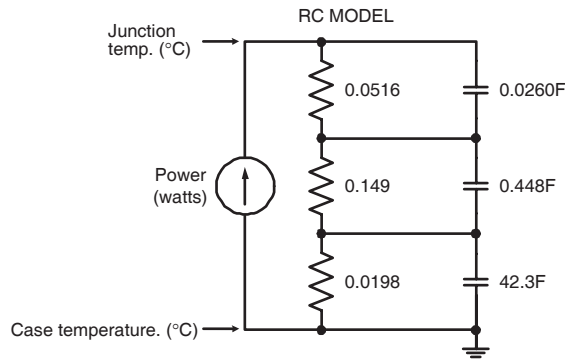


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

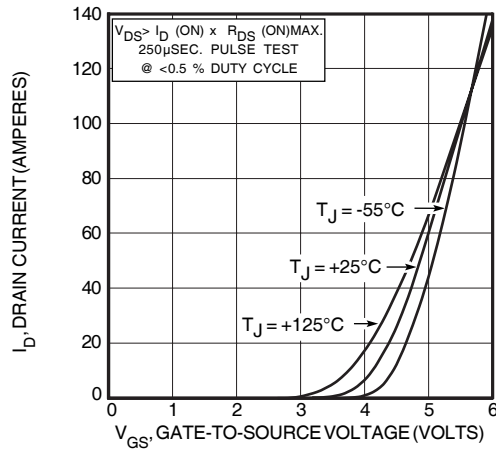


FIGURE 4, TRANSFER CHARACTERISTICS

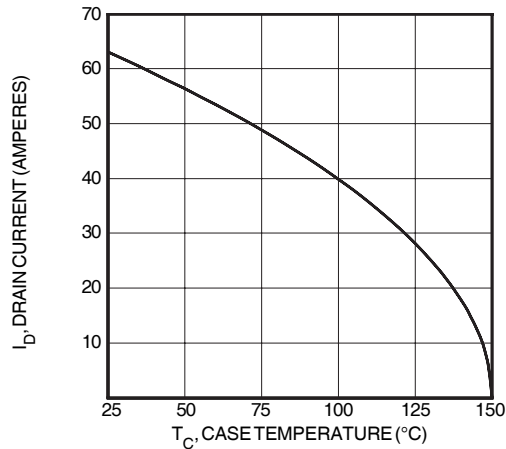


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

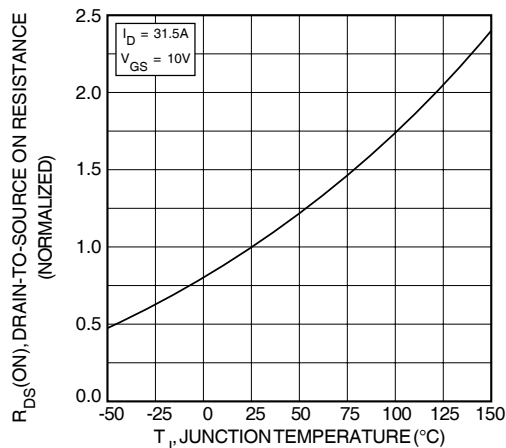


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

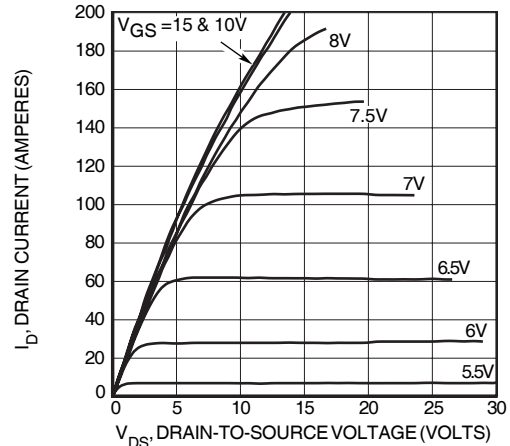


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

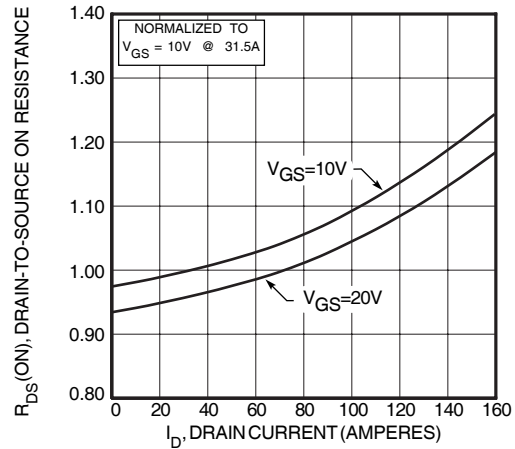


FIGURE 5, $R_{DS} (\text{ON})$ vs DRAIN CURRENT

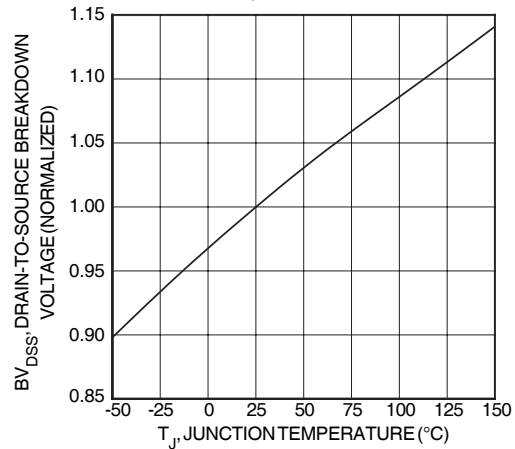


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

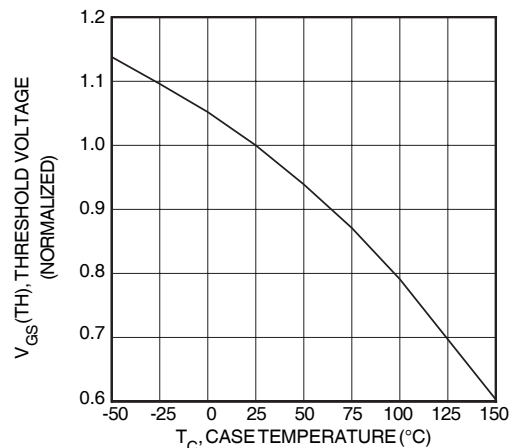


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

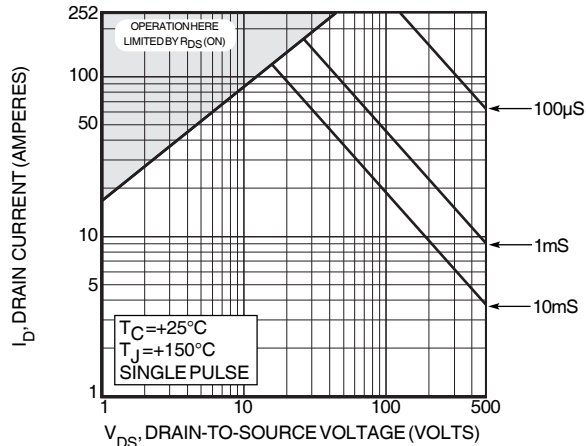


FIGURE 10, MAXIMUM SAFE OPERATING AREA

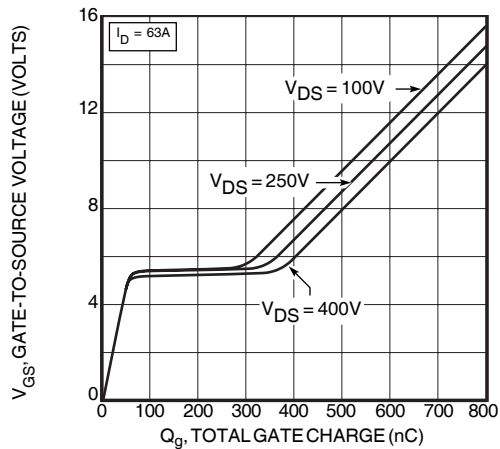


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

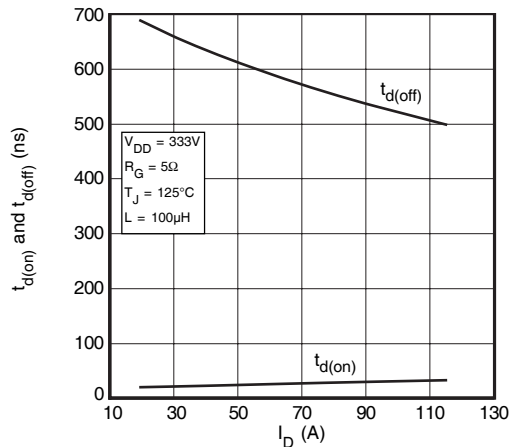


FIGURE 14, DELAY TIMES vs CURRENT

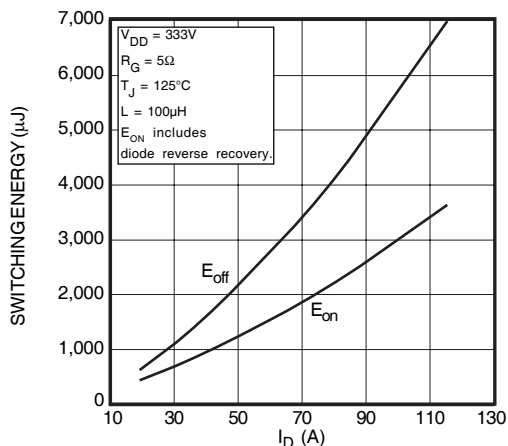


FIGURE 16, SWITCHING ENERGY vs CURRENT

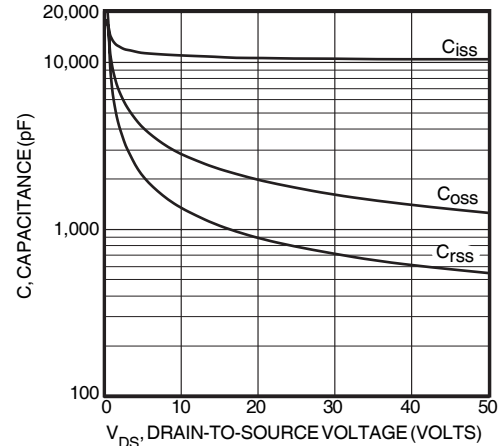


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

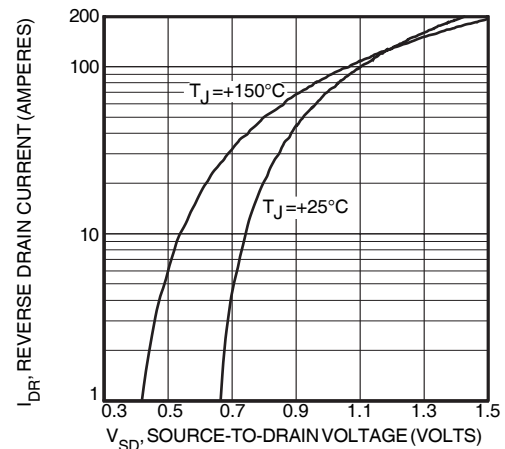


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

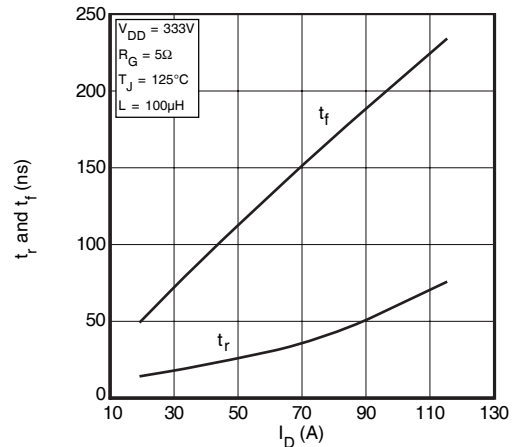


FIGURE 15, RISE AND FALL TIMES vs CURRENT

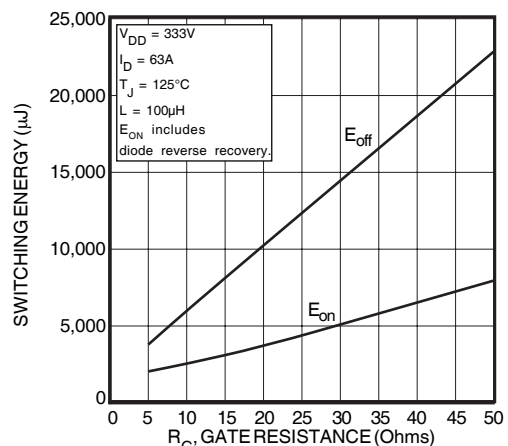


FIGURE 17, SWITCHING ENERGY VS. GATE RESISTANCE

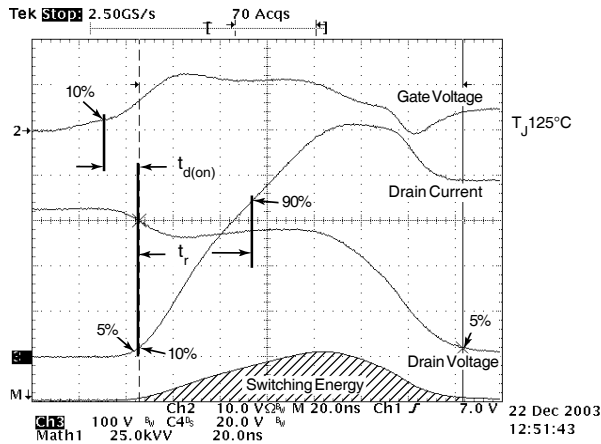


Figure 18, Turn-on Switching Waveforms and Definitions

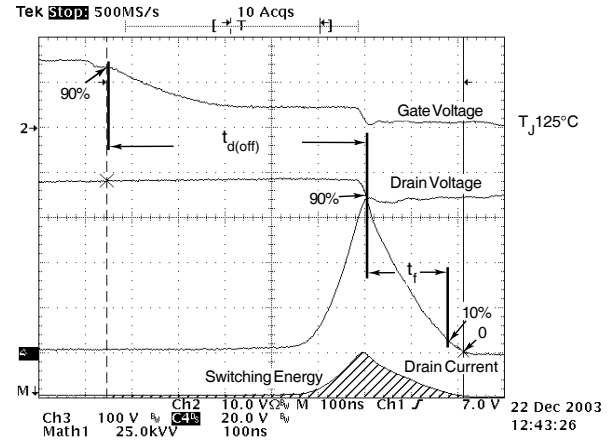


Figure 19, Turn-off Switching Waveforms and Definitions

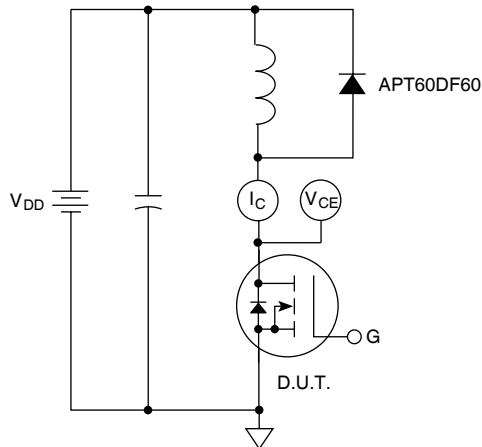


Figure 20, Inductive Switching Test Circuit

SOT-227 (ISOTOP®) Package Outline

